

INK021ABS1

High Speed Switching
Silicon N-channel MOSFET

DESCRIPTION

INK021ABS1 is a Silicon N-channel MOSFET.

This product is most suitable for use such as portable machinery, because voltage drive and low on resistance.

FEATURE

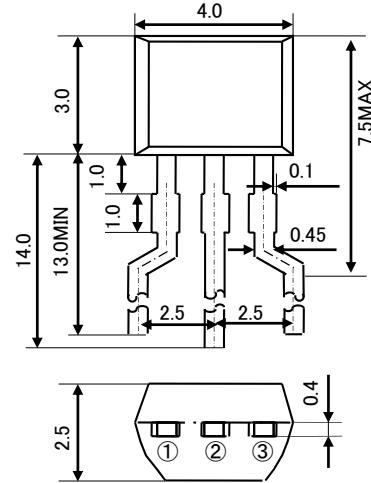
- Input impedance is high, and not necessary to consider a drive electric current.
- High drain current. $I_D=1.4A$
- V_{th} is low, and drive by low voltage is possible. $V_{th}=1.0\sim 2.5V$
- Low on Resistance. $R_{DS(on)}=0.2\ \Omega$ (TYP)
- High power Dissipation. $P_D=600mW$

APPLICATION

Switching

OUTLINE DRAWING

Unit: mm



TERMINAL CONNECTOR

- ①: SOURCE
- ②: DRAIN
- ③: GATE

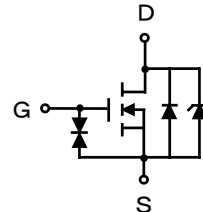
JEITA:
JEDEC:

MAXIMUM RATINGS ($T_a=25^\circ C$)

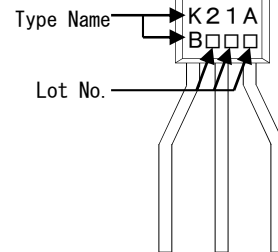
Symbol	Parameter	Rating	Unit
V_{DSS}	Drain-Source Voltage	100	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Drain Current(DC)	1.4	A
I_{DP}	Drain current(Pulse)	2(※1)	A
		8(※2)	
P_D	Total Power Dissipation	600	mW
T_{ch}	Channel Temperature	+150	$^\circ C$
T_{stg}	Storage temperature	-55~+150	$^\circ C$

※1 Single pulse $P_w \leq 3s$ ※2 Single pulse $P_w \leq 1ms$

EQUIVALENT CIRCUIT



MARKING



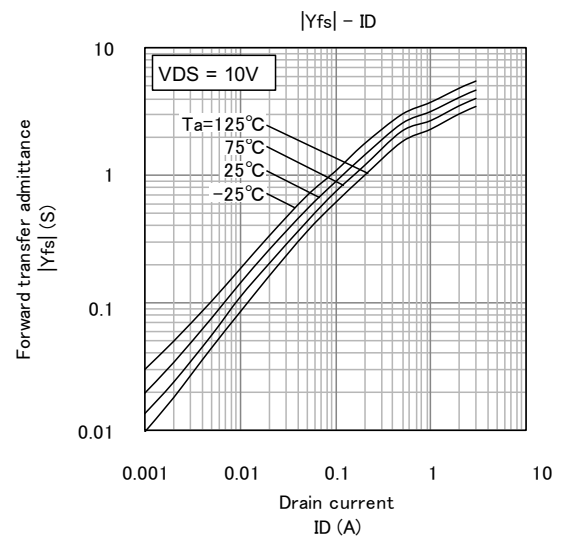
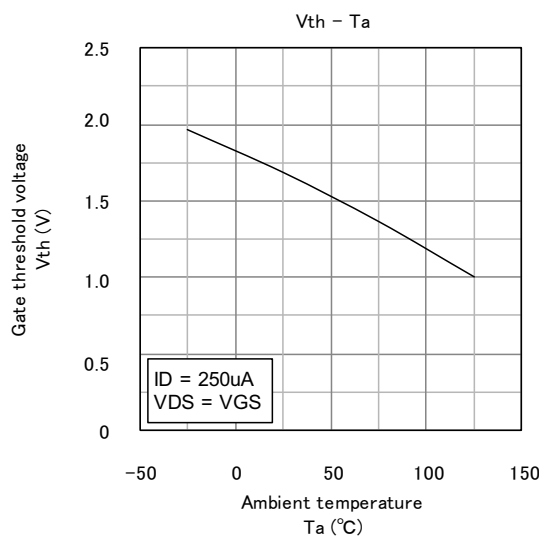
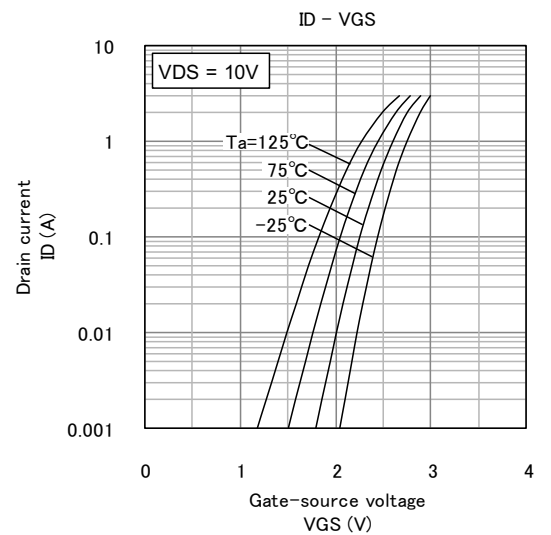
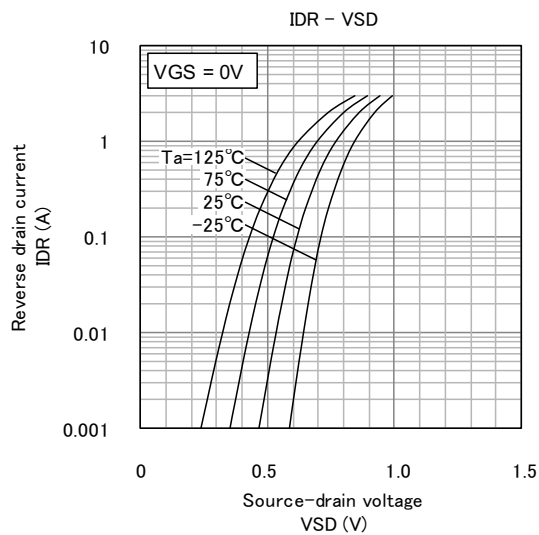
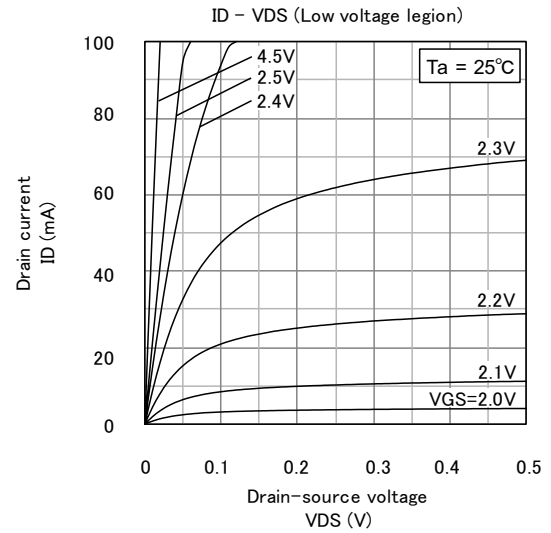
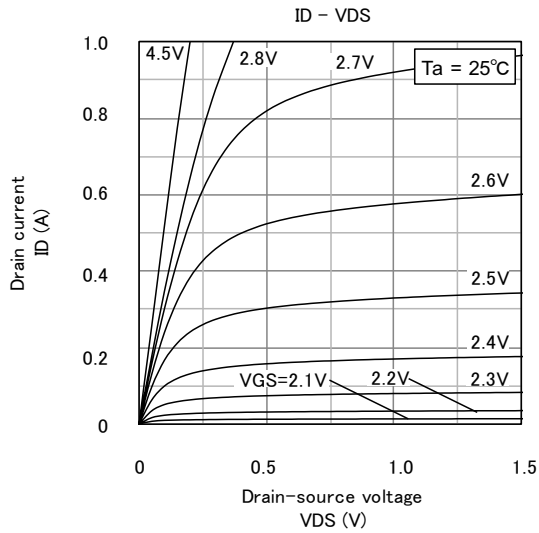
ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

Parameter	Symbol	Test Condition	Limit			Unit
			MIN	TYP	MAX	
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=100\ \mu A, V_{GS}=0V$	100	-	130	V
Gate-Source Leak current	I_{GSS}	$V_{GS}=\pm 20V, I_{DS}=0A$	-	-	± 10	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$	-	-	1	μA
Gate Threshold Voltage	V_{th}	$I_D=250\ \mu A, V_{DS}=V_{GS}$	1.0	-	2.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS}=10V, I_D=1A$	-	3.6	-	S
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$I_D=1A, V_{GS}=4.5V$	-	0.2	0.3	Ω
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V, f=1MHz$	-	660	-	pF
Output Capacitance	C_{oss}		-	80	-	pF
Switching Time	t_{on}	$V_{DD}=30V, I_D=1A$	-	580	-	ns
	t_{off}	$V_{GS}=0\sim 5V$	-	910	-	ns

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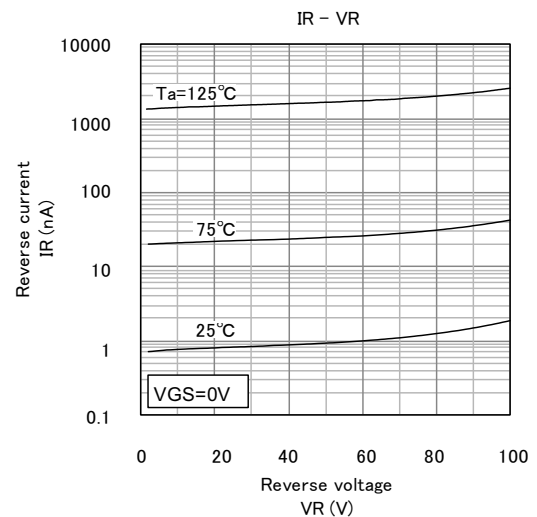
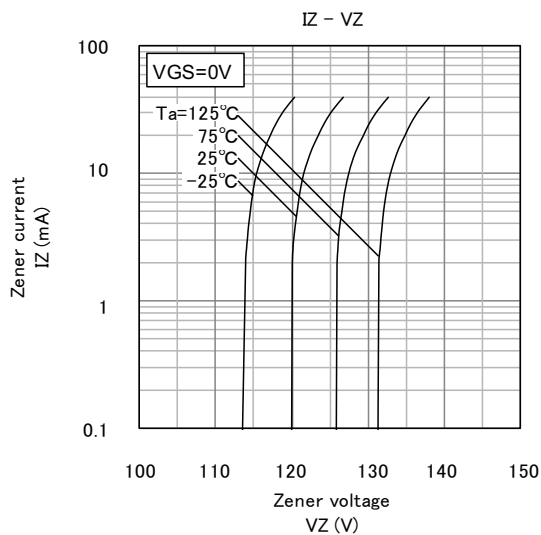
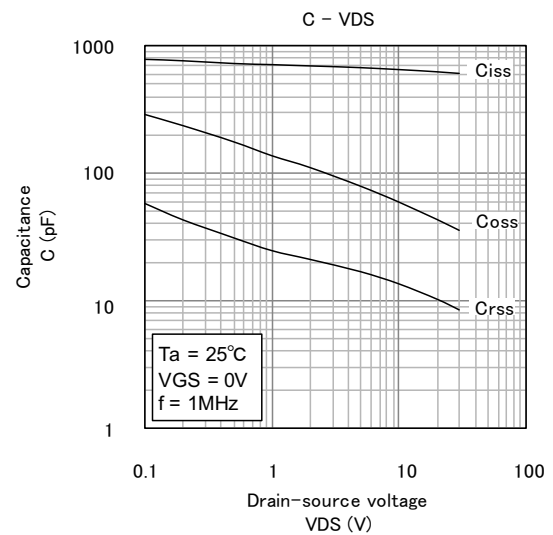
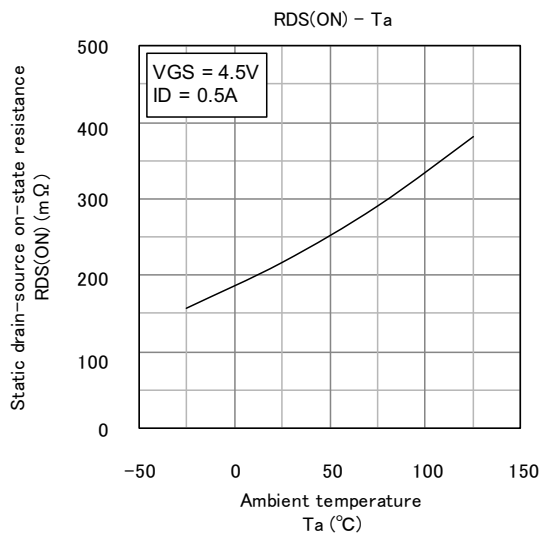
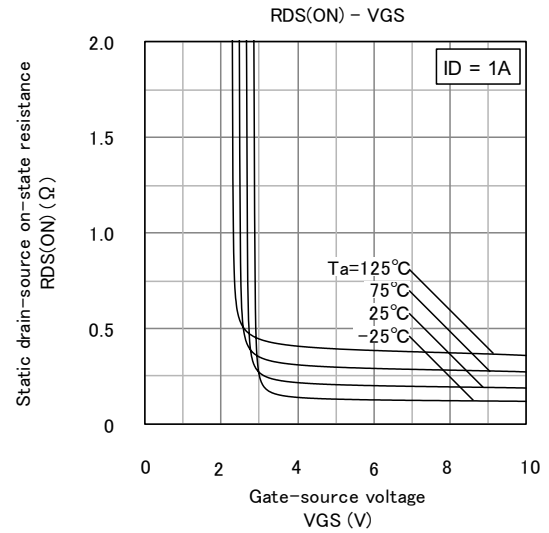
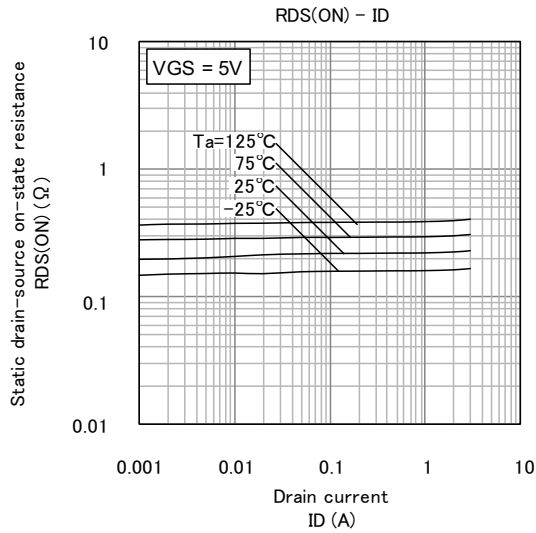
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TYPICAL CHARACTERISTICS



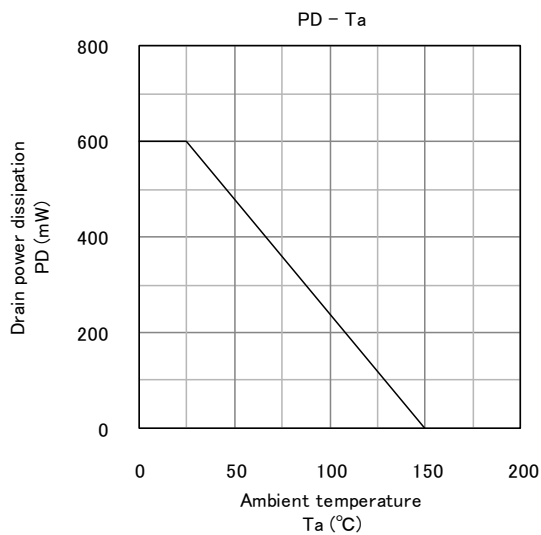
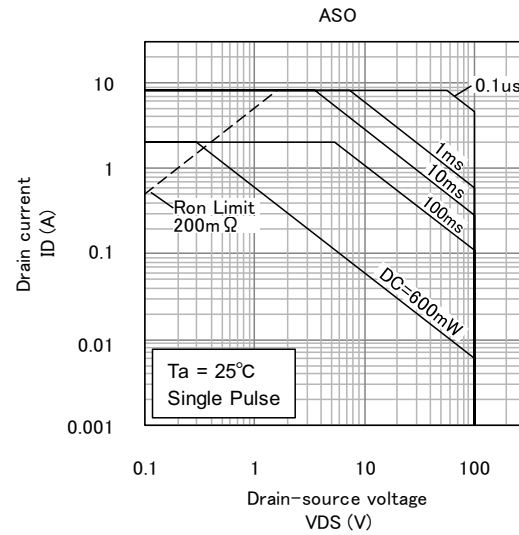
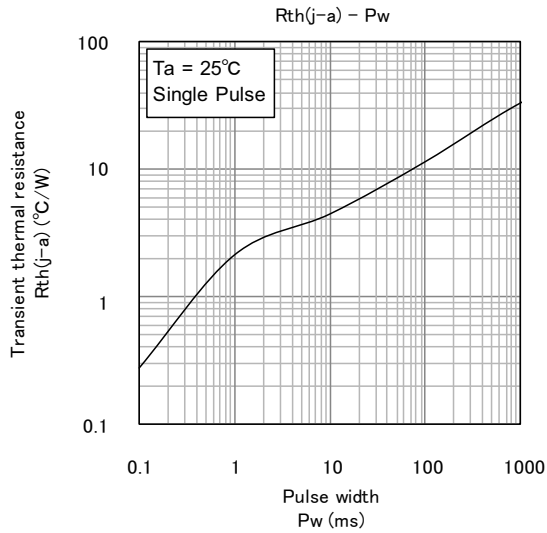
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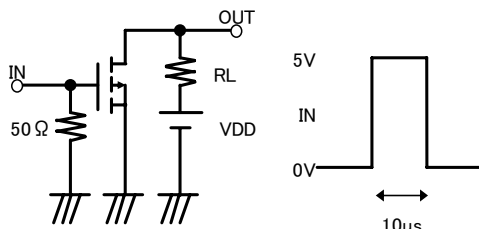


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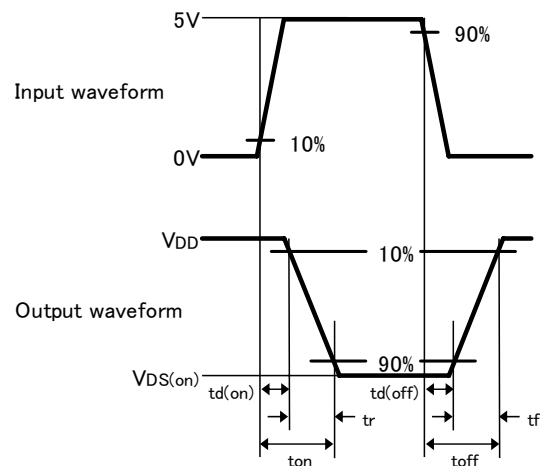
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Switching time test condition



Duty $\leq 1\%$
Input: $t_r, t_f < 10\text{ns}$
VDD = 30V
Common source
 $T_a = 25^{\circ}\text{C}$





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